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Sheet 1 of 8

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Application Number	10/026,019
Filing Date	December 27, 2001
First Named Inventor	Ralph Johnson
Group Art Unit	2828
Examiner Name	Tuan M Nguyen
Attorney Docket Number	V637-02674 US

✓	SEKIGUCHI, S., et al., "Long wavelength GaInAsP/InP laser with n-n contacts using AlAs/InP hole injecting tunnel junction", article, Japanese Journal of Applied Physics, Part 2, No 48, 04-15-1989, pgs L443-5.
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	SUGIMOTO, M., et al., "Surface emitting devices with distributed Bragg reflectors grown by highly precise molecular beam epitaxy", article, Journal of Crystal Growth, Vol 127, 1993, pgs 1-4.
	UCHIDA, T., et al., "CBE grown 1.5 μm GaInAsP-InP surface emitting lasers", article, IEEE Journal of Quantum Electronics, Vol 29, No 6, Jun 1993, pgs 1975-89.
	VAN DE WALLE, C., "Band lineups and deformation potentials in the model-solid theory", article, Physical Review B, Vol 39, No 3, 01-15-1989, pgs 1871-83.
	WHITAKER, T., "Long wavelength VCSELs move closer to reality", article, Compound Semiconductor, July 2000, pgs 65-7.
	YAMADA, M., et al., "Low-threshold lasing at 1.3 μm from GaAsSb quantum wells directly grown on GaAs substrates", article, IEEE, 0-7803-4947, 04/1998, pgs 189-90.
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	YANG, X., et al., "High performance 1.3 μm InGaAsN:Sb/GaAs quantum well lasers grown by molecular beam epitaxy", journal article, Journal of Vacuum Science and Technology B Microelectronics and Nanometer Structures, Vol. 18, No 3, Oct 1999, pgs 1484-7.
	YANG, X., et al., "InGaAsNSb/GaAs quantum wells for 1.55 μm lasers grown by molecular-beam epitaxy", article, Applied Physics Letters, Vol 78, No 26, pgs 4068-70. <i>(Cited by PCT Application No. PCT/US02/03476)</i>
↓	YANO, M., et al., "Time-resolved reflection high energy electron diffraction analysis for atomic layer depositions of GaSb by molecular beam epitaxy", article, Journal of Crystal Growth, Vol 148, 1995, pgs 349-53
↓	YUEN, W., et al., "High-performance 1.6 μm single-epitaxy top-emitting VCSEL", article, Electronics Letters, Vol 36, No 13, 06-22-2000, pgs 1121-3.

Examiner Signature	<i>W</i>	Date Considered	03/04/04
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EXAMINER: Initial if reference is considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to Applicant.

*Applicant's unique citation designation number (optional). *Applicant is to place a check mark here if English language Translation is attached.

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